

**Amendments to the Claims:**

This listing of claims will replace all prior versions and listing, of claims in the application:

**Listing of Claims:**

Claim 1 (currently amended): A semiconductor photo detecting device,  
comprising:  
a semiconductor substrate having a flat side face; and  
a photo absorption layer formed on said semiconductor substrate,  
wherein an entire part of said flat side face is inclined to a line perpendicular to a  
~~principle~~ principal plane of said semiconductor substrate[; and] ,  
wherein said flat side face is substantially perpendicular to an incoming photo  
signal,  
wherein said flat side face is a cleavage face of said semiconductor substrate, and  
wherein said semiconductor substrate has another side face parallel to said flat side  
face.

Claim 2 (canceled)

Claim 3 (canceled)

Claim 4 (original): The semiconductor photo detecting device as claimed in claim 1, wherein said semiconductor substrate is a III-V group compound semiconductor substrate, and said flat side face is one of a (110) plane and a (111) plane.

Claim 5 (currently amended): The semiconductor photo detecting device as claimed in claim 1, wherein said flat side face is inclined to a line perpendicular to said ~~principle~~ principal plane at an angle of 30° or less.

Claim 6 (currently amended): The semiconductor photo detecting device as claimed in claim 4, wherein said ~~principle~~ principal plane of said semiconductor substrate is inclined to a (100) plane ~~of said semiconductor substrate~~.

Claim 7 (original): The semiconductor photo detecting device as claimed in claim 1, wherein said side face is covered by an anti-reflection film.

Claim 8 (original): The semiconductor photo detecting device as claimed in claim 1, wherein said photo absorption layer is formed in a range in which a perpendicular line to said flat side face crosses.

Claim 9 (original): The semiconductor photo detecting device as claimed in claim 1, further comprising,

a first cap layer formed on said photo absorption layer; and  
an ohmic electrode formed on said cap layer.

Claim 10 (original): The semiconductor photo detecting device as claimed in claim 1, further comprising:

a cap layer formed on said photo absorption layer; and  
a second conduction type region formed in a part of said photo absorption layer and said cap layer,

wherein

said photo absorption layer and said cap layer are a first conduction type; and  
said photo absorption layer is formed in a range in which a perpendicular line to said flat side face crosses.

Claim 11 (withdrawn): A manufacturing method of a semiconductor photo detecting device, comprising,

a step of forming semiconductor layers including a photo absorption layer on an inclined semiconductor substrate,

a step of forming semiconductor photo detecting devices including said photo

absorption layer by patterning said semiconductor photo detecting devices in multiple parts of said inclined semiconductor substrate,

a step of dividing said semiconductor substrate into multiple semiconductor photo detecting devices having one or more pairs of cleavage faces by cleaving said semiconductor substrate, and,

a step of forming an anti-reflection film on said cleavage faces.